勝特力材料 886-3-5753170 胜特力电子(上海) 86-21-54151736 胜特力电子(深圳) 86-755-83298787 Http://www. 100y. com. tw

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Preferred Device

General Purpose Transistor

PNP Silicon

Features

• Pb-Free Packages are Available

MAXIMUM RATINGS

• FU-Fiee Fackages are Available			
MAXIMUM RATINGS			
Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-40	Vdc
Collector-Base Voltage	V _{CBO}	-40	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	lc	-200	mAdc

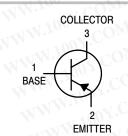
THERMAL CHARACTERISTICS

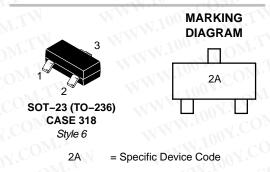
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$	P _D	225	mW
Derate above 25°C	[1.8	mW/°C
Thermal Resistance Junction to Ambient	R _{0JA}	556	°C/W
Total Device Dissipation	PD	300	mW
Alumina Substrate, (Note 2) $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$		2.4	mW/°C
Thermal Resistance Junction-to-Ambient	R_{\thetaJA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	–55 to +150	°C

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

ON Semiconductor®





ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT3906LT1	SOT-23	3000 / Tape & Reel
MMBT3906LT1G	SOT-23	3000 / Tape & Reel
MMBT3906LT3	SOT-23	10000 / Tape & Reel
MMBT3906LT3G	SOT-23	10000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

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WW.IO	ELECTRICAL CHARA	CTERISTICS (T _A = 25°C unless otherwise note	ed)
WW.100		MMBT3906	
W.10		MMDT2006	т 19

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	NWW.Inony.C	ONT.	V	
Collector – Emitter Breakdown Voltage ($I_{C} = -1.0 \text{ mAdc}, I_{B} = 0$)	V _{(BR)CEO}	-40		Vdc
Collector – Base Breakdown Voltage ($I_C = -10 \ \mu Adc$, $I_E = 0$)	V _{(BR)CBO}	-40		Vdc
Emitter – Base Breakdown Voltage ($I_E = -10 \ \mu Adc$, $I_C = 0$)	V _{(BR)EBO}	-5.0		Vdc
Base Cutoff Current ($V_{CE} = -30$ Vdc, $V_{EB} = -3.0$ Vdc)	IBL	N.C	-50	nAdc
Collector Cutoff Current ($V_{CE} = -30$ Vdc, $V_{EB} = -3.0$ Vdc)	I _{CEX}	102-00	-50	nAdc
ON CHARACTERISTICS (Note 3)	WWW.	N.C.	VT 1	
				1

ON CHARACTERISTICS (Note 3)

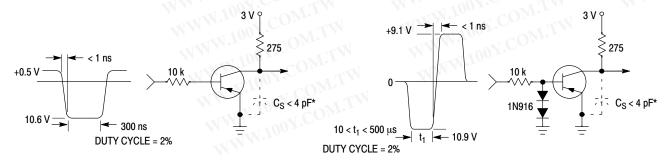
ON CHARACTERISTICS (Note 3)	WWW.	N.C.	VTI	
$ \begin{array}{l} \text{DC Current Gain} \\ (I_{C} = -0.1 \text{ mAdc}, \text{ V}_{CE} = -1.0 \text{ Vdc}) \\ (I_{C} = -1.0 \text{ mAdc}, \text{ V}_{CE} = -1.0 \text{ Vdc}) \\ (I_{C} = -10 \text{ mAdc}, \text{ V}_{CE} = -1.0 \text{ Vdc}) \\ (I_{C} = -50 \text{ mAdc}, \text{ V}_{CE} = -1.0 \text{ Vdc}) \\ (I_{C} = -100 \text{ mAdc}, \text{ V}_{CE} = -1.0 \text{ Vdc}) \end{array} $	TW WWW	60 80 100 60 30	 300 	17 17 17 17 17 17 17 17 17 17 17 17 17 1
Collector – Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc}$) ($I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$)	V _{CE(sat)}	N. <u>14</u> .10	-0.25 -0.4	Vdc
Base – Emitter Saturation Voltage $(I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc})$ $(I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc})$	V _{BE(sat)}	-0.65 —	-0.85 -0.95	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product ($I_C = -10 \text{ mAdc}$, $V_{CE} = -20 \text{ Vdc}$, f = 100 MHz)	fT	250	W.100	MHz
Output Capacitance (V _{CB} = -5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	-11	4.5	pF
Input Capacitance ($V_{EB} = -0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C _{ibo}	-4	10	pF
Input Impedance ($I_C = -1.0 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h _{ie}	2.0	12	kΩ
Voltage Feedback Ratio ($I_C = -1.0$ mAdc, $V_{CE} = -10$ Vdc, f = 1.0 kHz)	h _{re}	0.1	10	X 10 ⁻⁴
Small-Signal Current Gain ($I_C = -1.0$ mAdc, $V_{CE} = -10$ Vdc, f = 1.0 kHz)	h _{fe}	100	400	Too V
Output Admittance ($I_C = -1.0$ mAdc, $V_{CE} = -10$ Vdc, f = 1.0 kHz)	h _{oe}	3.0	60	μmhos
Noise Figure (I _C = -100μ Adc, V _{CE} = $-5.0 $ Vdc, R _S = $1.0 $ kΩ, f = $1.0 $ kHz)	NF	_	4.0	dB

Delay Time 35 td $(V_{CC} = -3.0 \text{ Vdc}, V_{BE} = 0.5 \text{ Vdc},$ $I_{\rm C} = -10$ mAdc, $I_{\rm B1} = -1.0$ mAdc) **Rise Time** 35 tr Storage Time 225 ts $(V_{CC} = -3.0 \text{ Vdc}, I_{C} = -10 \text{ mAdc},$ _ $I_{B1} = I_{B2} = -1.0 \text{ mAdc}$ Fall Time 75 tf _

3. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.



* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time **Equivalent Test Circuit**

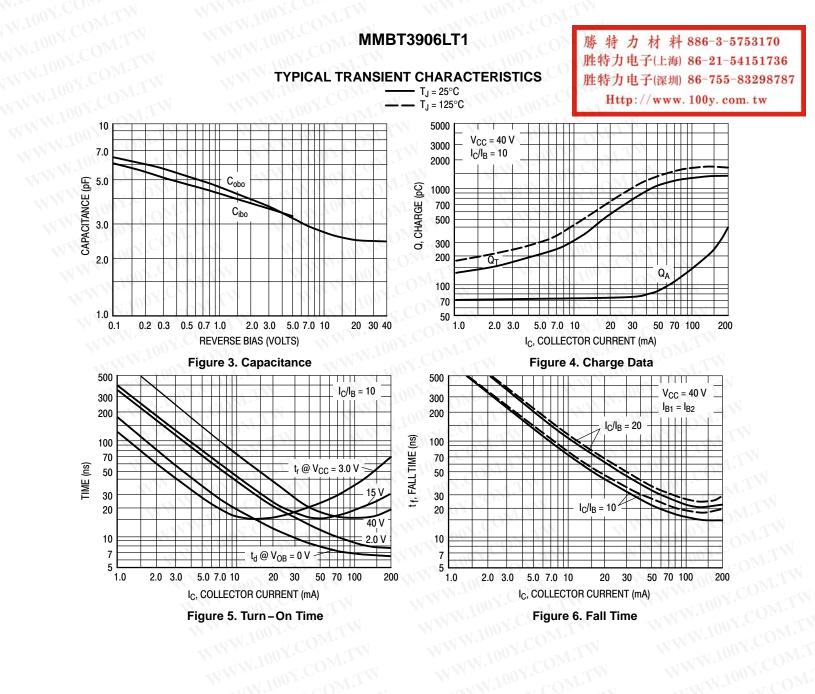
Figure 2. Storage and Fall Time **Equivalent Test Circuit**

ns

ns

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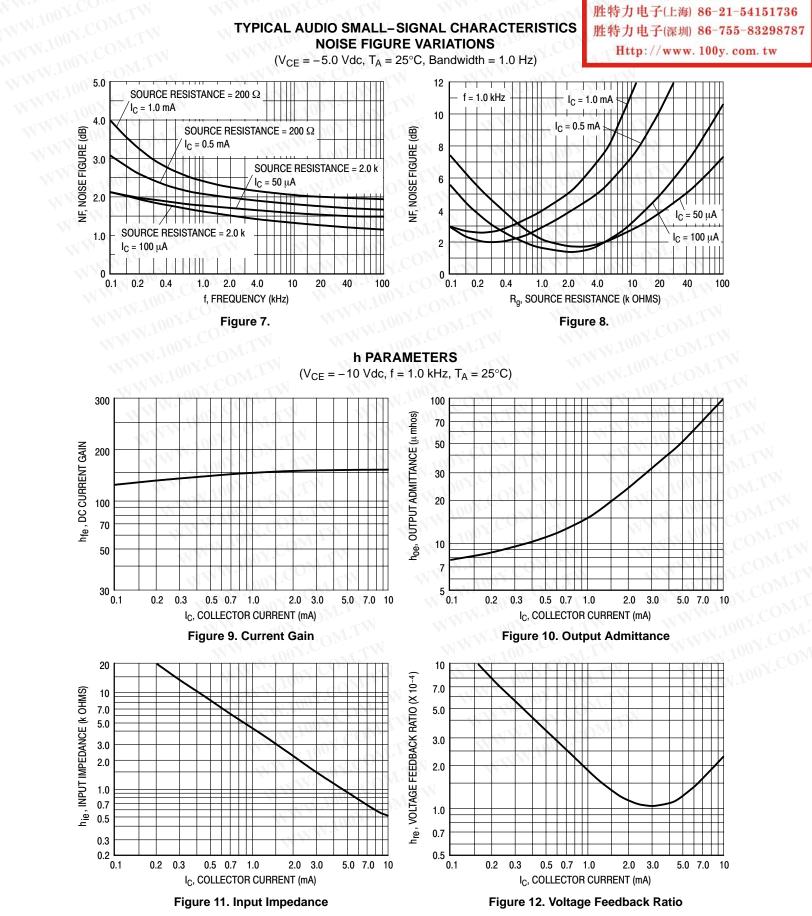
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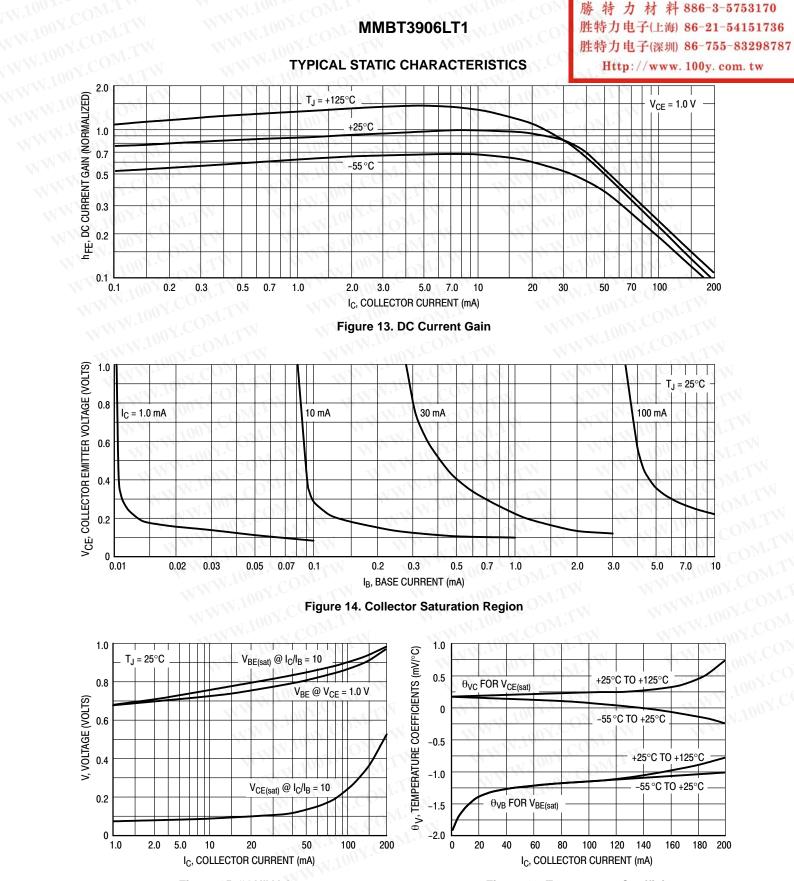


Figure 15. "ON" Voltages

Figure 16. Temperature Coefficients

100Y.COM PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AH**



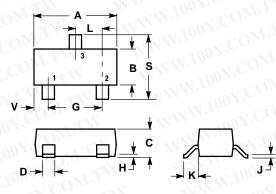
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH. 2
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS 3. IS THE MINIMUM THICKNESS OF BASE MATERIAL
- 4. 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.

	INC	CHES	MILLIMETER	
DIM	MIN	MAX	MIN	MAX
Α	0.1102	0.1197	2.80	3.04
В	0.0472	0.0551	1.20	1.40
С	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
н	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
Κ	0.0140	0.0285	0.35	0.69
. L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
٧	0.0177	0.0236	0.45	0.60

PIN 1. BASE FMITTER 2.





SOLDERING FOOTPRINT

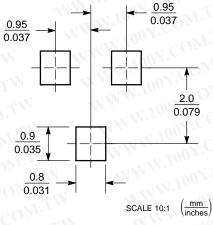


Figure 17. SOT-23

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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